

2SD734

NPN Silicon Epitaxial Planar Transistor

for 1W Output, Electronic Governor, DC-DC Converter Applications.

The transistor is subdivided into four groups D, E, F and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	25	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	700	mA
Collector Current (Pulse)	I_{CP}	1500	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at V _{CE} = 2 V, I _C = 50 mA	Current Gain Group D E F G	h _{FE}	60	-	120	-
		h _{FE}	100	-	200	-
		h _{FE}	160	-	320	-
		h _{FE}	280	-	560	-
		h _{FE}	50	-	-	-
at V _{CE} = 2 V, I _C = 500 mA						
Collector Base Cutoff Current at V _{CB} = 20 V	I _{CBO}	-	-	1	μA	
Emitter Base Cutoff Current at V _{EB} = 4 V	I _{EBO}	-	-	1	μA	
Gain Bandwidth Product at V _{CE} = 10 V, I _C = 50 mA	f _T	-	250	-	MHz	
Output Capacitance at V _{CB} = 10 V, f = 1 MHz	C _{ob}	-	8	-	pF	

